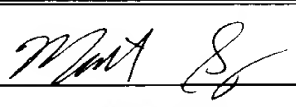


(Rev. 5/92) Comparable to Form PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. 82821		Serial No. 09/856,212		
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				Applicant NAKAMURA et al.				
				Filing Date May 18, 2001		Group 1765		
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
MJ		6,153,008	11/28/2000	Von Ammon et al.	—	—	—	
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Name of Patentee	Class	Subclass	Translation Yes No	
MJ		WO 98/45508	10/15/1998	MEMC Electronic Materials, Inc.	—	—	X	
MJ		WO 98/45508	10/15/1998	MEMC Electronic Materials, Inc.	—	—	X	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
MJ		NAKAMURA, KOZO et al.: "Formation process of grown-in defects in Czochralski grown silicon crystals" JOURNAL OF CRYSTAL GROWTH 180 (1997) 61-72						
MJ		AMMON, WILFRIED VON et al.: "The dependence of bulk defects on the axial temperature gradient of silicon crystals during Czochralski growth" 2300 JOURNAL OF CRYSTAL GROWTH 151 (1995) June I, Nos. 3/4, Amsterdam, NL, Pages 273-277						
Examiner 				Date Considered 5/2/2002				
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								